L Number	Hits	Search Text	DB	Time stamp
1	2886573	memory or storage	USPAT;	2004/09/01 15:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	395	(memory or storage) and flash and sonos	USPAT;	2004/09/01 15:25
			US-PGPUB;	
		*	EPO; JPO;]
			DERWENT	
3	1316	(memory or storage) and silicon adj oxide adj nitride	USPAT;	2004/09/01 15:27
			US-PGPUB;	
			EPO; JPO;	
4	1502	(/maman, av abavana) and flock and access) (/maman	DERWENT	2004/00/04 45 27
4	1563	((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 15:27
		storage) and silicon adj oxide adj nitride)	US-PGPUB;	
			EPO; JPO; DERWENT	
5	27	(((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 16:21
١	2,	storage) and silicon adj oxide adj nitride)) and program\$7	US-PGPUB;	2004/09/01 16:21
		with hot adj electron with nitride	EPO; JPO;	
		War not day close on with manac	DERWENT	
6	15	((((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 15:29
		storage) and silicon adj oxide adj nitride)) and program\$7	US-PGPUB;	2001/05/01 15:25
		with hot adj electron with nitride) and (voltage or potential	EPO; JPO;	
		or level) with substrate	DERWENT	
7	15	(((((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 15:30
		storage) and silicon adj oxide adj nitride)) and program\$7	US-PGPUB;	, . ,
		with hot adj electron with nitride) and (voltage or potential	EPO; JPO;	
		or level) with substrate) and (voltage or potential or level)	DERWENT	
		with gate		
8	10	((((((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 16:06
		storage) and silicon adj oxide adj nitride)) and program\$7	US-PGPUB;	
		with hot adj electron with nitride) and (voltage or potential	EPO; JPO;	
		or level) with substrate) and (voltage or potential or level)	DERWENT	
	10	with gate) and (fowler or hot adj hole)	LICDAT	2004/00/04 46:07
9	10	(((((((memory or storage) and flash and sonos) ((memory	USPAT;	2004/09/01 16:07
		or storage) and silicon adj oxide adj nitride)) and program\$7 with hot adj electron with nitride) and (voltage or potential	US-PGPUB; EPO; JPO;	
		or level) with substrate) and (voltage or potential or level)	DERWENT	
		with gate) and (fowler or hot adj hole)) and eras\$5	DERWEIT	
10	11	(((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 16:23
		storage) and silicon adj oxide adj nitride)) and eras\$5 with	US-PGPUB;	200 1, 05, 01 10.20
		(fowler or hot adj hole) with (voltage or potential or level)	EPO; JPO;	
		with substrate	DERWENT	
11	87	(((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 16:23
		storage) and silicon adj oxide adj nitride)) and eras\$5 with	US-PGPUB;	
		float\$5 with (drain or source)	EPO; JPO;	
			DERWENT	
12	5	((((memory or storage) and flash and sonos) ((memory or	USPAT;	2004/09/01 16:23
		storage) and silicon adj oxide adj nitride)) and eras\$5 with	US-PGPUB;	
		(fowler or hot adj hole) with (voltage or potential or level)	EPO; JPO;	
		with substrate) and ((((memory or storage) and flash and	DERWENT	
		sonos) ((memory or storage) and silicon adj oxide adj		
		nitride)) and eras\$5 with float\$5 with (drain or source))	<u> </u>	L